TOSHIBA Photocoupler GaAs Ired & Photo-Thyristor

TLP741G

Office Machine
Household Use Equipment
Solid State Relay
Switching Power Supply

The TOSHIBA TLP741G consists of a photo-thyristor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

- Peak off-state voltage: 400V(min.)
- Trigger LED current: 10mA(max.)
- On-state current: 150mA(max.)
- UL recognized: UL1577, file no. E67349
- BSI approved: BS EN60065: 2002 Certificate no. 8877

BS EN60950-1: 2002 Certificate no. 8878

- Isolation voltage: 4000V_{rms}(min.)
- Option (D4) type

VDE approved: DIN EN 60747-5-2

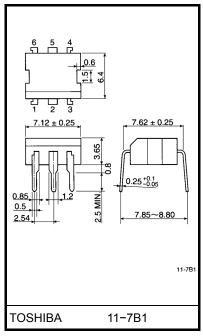
Certificate no. 40009302

Maximum operating insulation voltage: $630 V_{PK}$ Highest permissible over voltage: $6000 V_{PK}$

(Note) When a EN 60747-5-2 approved type is needed, please designate the "option (D4)"

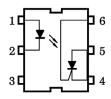
	7.62mm pich standard type	10.16mm pich (LF2) type
• Creepage distance:	7.0mm(min.)	8.0mm(min.)
Clearance:	7.0mm(min.)	8.0mm(min.)
Insulation thickness:	0.5mm(min.)	0.5mm(min.)

Unit in mm



Weight: 0.35 g

Pin Configuration (top view)



1 : ANODE 2 : CATHODE

3 : NC

4 : CATHODE 5 : ANODE 6 : GATE

Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	l _F	60	mA
	Forward current derating (Ta ≥ 39°C)	ΔI _F / °C	-0.7	mA / °C
LED	Peak forward current (100µs pulse, 100pps)	I _{FP}	1	Α
	Power dissipation	P _D	100	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _D / °C	-1.0	mW / °C
	Reverse voltage	V _R	5	V
	Junction temperature	Tj	125	°C
	Peak forward voltage($R_{GK} = 27k\Omega$)	V_{DRM}	400	V
	Peak reverse voltage(R _{GK} = 27kΩ)	V_{RRM}	400	V
	On-state current	I _{T(RMS)}	150	mA
Detector	On–state current derating (Ta ≥ 25°C)	ΔI _T / °C	-2.0	mA / °C
	Peak on-state current (100µs pulse, 120pps)	I _{TP}	3	Α
	Peak one cycle surge current	I _{TSM}	2	Α
	Peak reverse gate voltage	V_{GM}	5	V
	Power dissipation	P _D	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP _D / °C	-2.0	mW / °C
	Junction temperature	Tj	100	°C
Storage temperature range		T _{stg}	-55~125	°C
Operating temperature range		T _{opr}	-55~100	°C
Lead soldering temperature (10s)		T _{sol}	260	°C
Total p	package power dissipation	PT	250	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP _T / °C	-3.3	mW / °C
Isolatio	on voltage (AC, 1 min., R.H. ≤ 60%)	BVS	4000	V _{rms}

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	-	120	V _{ac}
Forward current	lF	15	20	25	mA
Operating temperature	T _{opr}	-25	_	85	°C
Gate to cathode resistance	R _{GK}	_	27	33	kΩ
Gate to cathode capacity	C _{GK}	_	0.01	0.1	μF

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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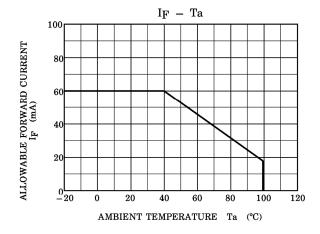
Individual Electrical Characteristics (Ta = 25°C)

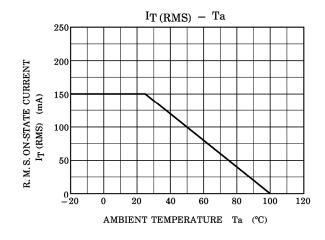
	Characteristic Symbol Test Condition		Min.	Тур.	Max.	Unit		
	Forward voltage	V _F	I _F = 10mA		1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5V		_	_	10	μΑ
Capacitance C_T $V = 0$,		V = 0, f = 1MHz	V = 0, f = 1MHz		30	_	pF	
or	Off-state current	I _{DRM}	V _{AK} = 400V R _{GK} = 27kΩ	Ta = 25°C	_	10	5000	nA
				Ta = 100°C	_	1	100	μA
	Reverse current	I _{RRM}	V _{KA} = 400V R _{GK} = 27kΩ	Ta = 25°C	_	10	5000	nA
				Ta = 100°C	_	1	100	μA
Detector	On-state voltage	V _{TM}	I _{TM} = 100mA	0mA		0.9	1.3	V
De	Holding current	lΗ	R _{GK} = 27kΩ		_	0.2	_	mA
	Off–state dv / dt	dv/dt	$V_D = 280V, R_{GK} = 27k\Omega$		5	10	_	V/µs
	Capacitance C_j $V = 0, 1$	C.	V = 0, f = 1MHz	Anode to gate	_	20	_	ηE
		V = 0, 1 = 11VIFIZ	Gate to cathode	_	350	_	pF	

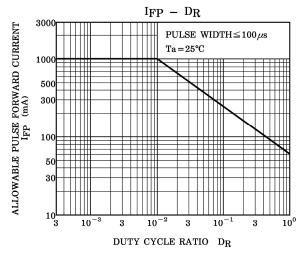
Coupled Characteristics (Ta = 25°C)

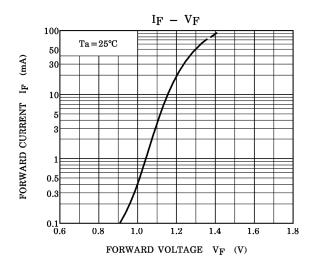
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit	
Trigger LED current	I _{FT}	V_{AK} = 6V, R_{GK} = 27k Ω	_	4	10	mA	
Turn-on time	ton	t_{ON} $I_{F} = 30 \text{mA}, V_{AA} = 50 \text{V}, \\ R_{GK} = 27 \text{k}\Omega$		10	_	μs	
Coupled dv/dt	dv/dt	$V_S = 500V$, $R_{GK} = 27k\Omega$	500	_	_	V/µs	
Capacitance (input to output)	CS	V _S = 0, f = 1MHz	_	0.8	_	pF	
solation resistance R _S V _S = 500V		V _S = 500V	1×10 ¹²	10 ¹⁴	_	Ω	
	BVS	AC, 1 minute	4000	_	_	V _{rms}	
Isolation voltage		AC, 1 second, in oil	_	10000	_		
		DC, 1 minute, in oil	_	10000	_	V _{dc}	

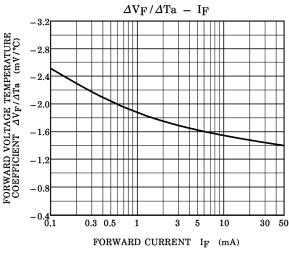
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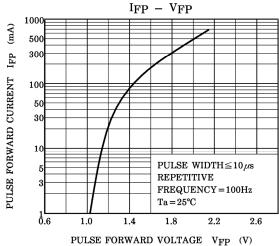


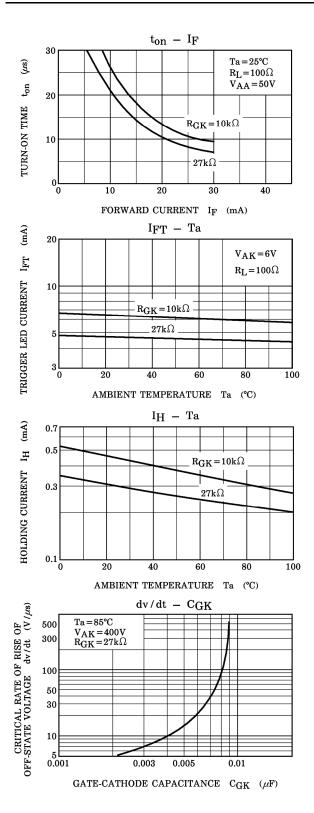


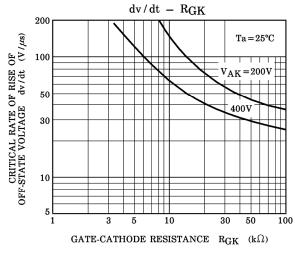


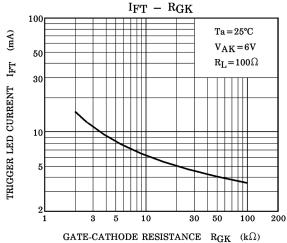


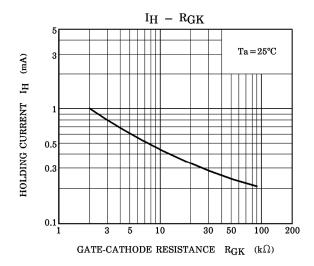












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RESTRICTIONS ON PRODUCT USE

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- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
 In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
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